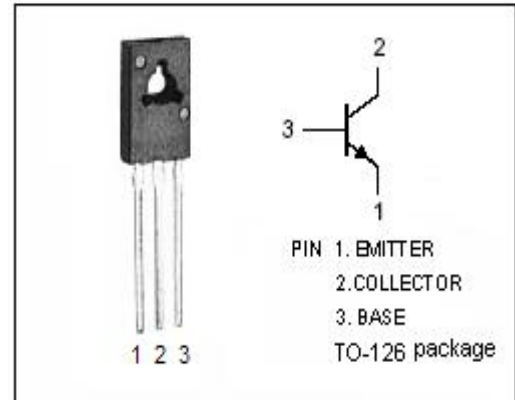


isc Silicon NPN Power Transistor
2SD1531
DESCRIPTION

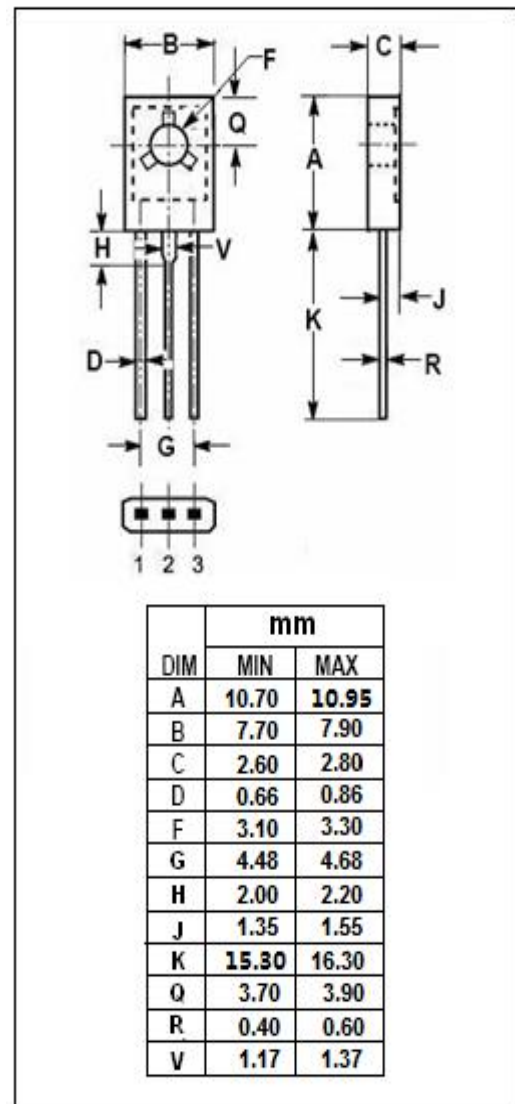
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 40V(\text{Min})$
- Good Linearity of h_{FE}
- Low Collector Saturation Voltage
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for AF output amplifier applications.


ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

| SYMBOL | PARAMETER | VALUE | UNIT |
|-----------|---|---------|------------------|
| V_{CBO} | Collector-Base Voltage | 50 | V |
| V_{CEO} | Collector-Emitter Voltage | 40 | V |
| V_{EBO} | Emitter-Base Voltage | 5 | V |
| I_C | Collector Current-Continuous | 2 | A |
| I_{CP} | Collector Current-Peak | 4 | A |
| P_C | Collector Power Dissipation @ $T_C=25^\circ\text{C}$ | 5 | W |
| | Collector Power Dissipation @ $T_a=25^\circ\text{C}$ | 1.2 | |
| T_J | Junction Temperature | 150 | $^\circ\text{C}$ |
| T_{stg} | Storage Temperature Range | -55~150 | $^\circ\text{C}$ |



isc Silicon NPN Power Transistor

2SD1531

ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|---------------|--------------------------------------|---|-----|------|-----|---------------|
| $V_{(BR)CBO}$ | Collector-Base Breakdown Voltage | $I_C=1\text{mA}; I_E=0$ | 50 | | | V |
| $V_{(BR)CEO}$ | Collector-Emitter Breakdown Voltage | $I_C=2\text{mA}; I_B=0$ | 40 | | | V |
| $V_{CE(sat)}$ | Collector-Emitter Saturation Voltage | $I_C=3\text{A}; I_B=0.3\text{A}$ | | | 1.0 | V |
| $V_{BE(sat)}$ | Base-Emitter Saturation Voltage | $I_C=2\text{A}; I_B=0.2\text{A}$ | | | 1.5 | V |
| I_{CBO} | Collector Cutoff Current | $V_{CB}=50\text{V}; I_E=0$ | | | 1.0 | μA |
| I_{CEO} | Collector Cutoff Current | $V_{CE}=10\text{V}; I_B=0$ | | | 100 | μA |
| I_{EBO} | Emitter Cutoff Current | $V_{EB}=5\text{V}; I_C=0$ | | | 10 | μA |
| h_{FE} | DC Current Gain | $I_C=1\text{A}; V_{CE}=5\text{V}$ | 50 | 120 | 220 | |
| f_T | Current-Gain—Bandwidth Product | $I_C=0.5\text{A}; V_{CE}=5\text{V}$ | | 150 | | MHz |
| C_{OB} | Collector Output Capacitance | $I_E=0; V_{CB}=20\text{V}; f=1\text{MHz}$ | | 20 | | pF |

◆ h_{FE} Classifications

| P | Q | R |
|--------|--------|---------|
| 50-100 | 80-160 | 120-220 |

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